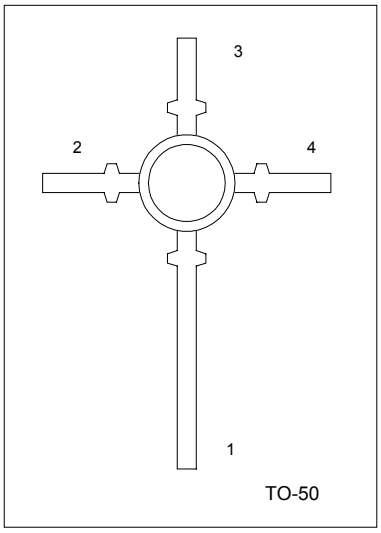
UTC 2SC3358 NPN SILICON EPITAXIALTRANSISTOR

HIGH FREQUENCY LOW NOISE AMPLIFIER



1:COLLECTOR 2:EMITTER 3:BASE 4:EMITTER

FEATURES

*Low Noise and High Gain
*High Power Gain

ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	20	V
Collector-emitter voltage	V_{CEO}	12	V
Emitter-base voltage	V_{EBO}	3	V
Collector current	Ic	100	mA
Total power dissipation	P_T	250	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-65 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cutoff Current	I_{CBO}	V_{CB}=10V, I_E=0			1.0	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=1V, I_C=0			1.0	μA
DC Current Gain	h_{FE}	V_{CE}=10V, I_C=20mA	50		300	
Gain bandwidth Product	fT	V_{CE}=10V, I_C=20mA		7		GHz
Feed-Back Capacitance	Cre	V_{CB}=10V, I_E=0, f=1.0MHz			1.0	pF
Noise figure	NF	V_{CE}=10V, I_C=7mA, f=1.0GHz			2.0	dB